

FIG. 1A

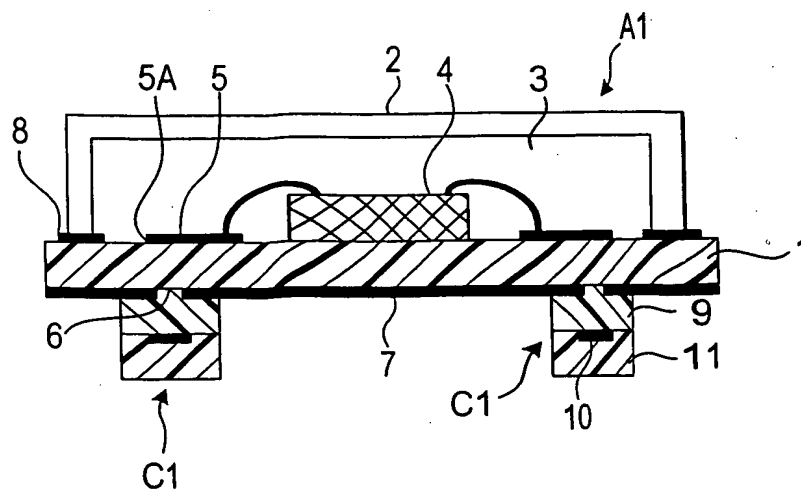
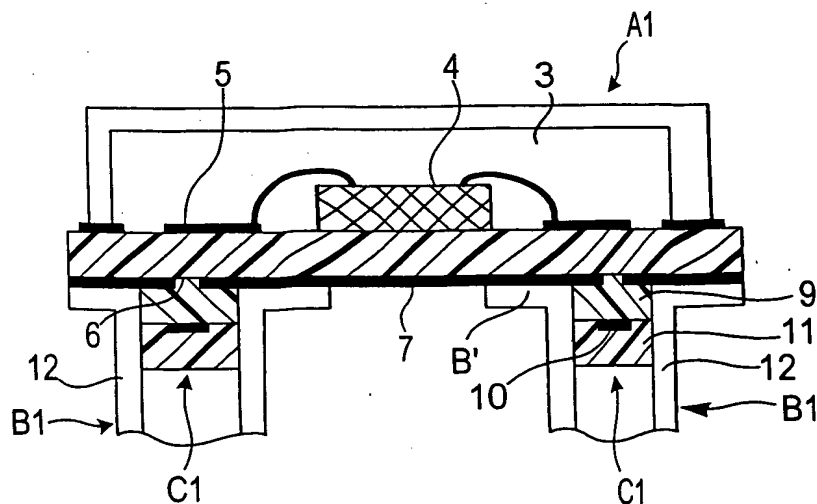


FIG. 1B



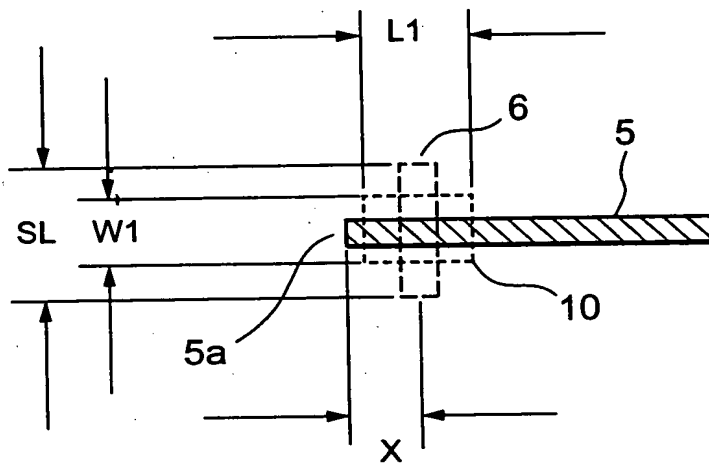
[illegible]

A cross-sectional view of a semiconductor device. A central channel, indicated by a cross-hatched pattern, is flanked by two regions with diagonal hatching. Below the channel, there are two large, U-shaped structures labeled C2. The top surface of the device is covered by a layer labeled A2. The bottom surface of the device is labeled B1. The side walls of the device are labeled B'. The central channel is labeled 18.

This cross-sectional view shows a semiconductor device. A central layer 7 is sandwiched between a substrate 13 and a base 18. The substrate 13 has a central region 13A. Electrical contacts A2, B1, B', and C2 are shown. A2 is a top contact, B1 and B' are side contacts, and C2 is a bottom contact. The central region 13A is connected to the central layer 7.



FIG.3



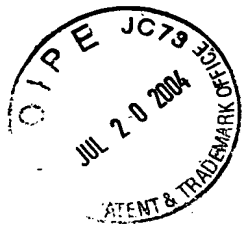


FIG. 4A

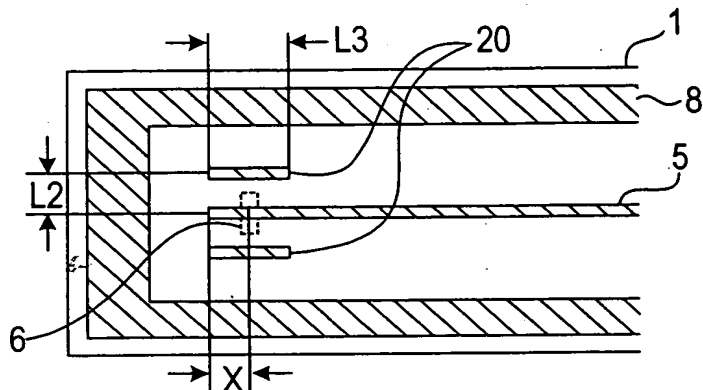


FIG. 4B

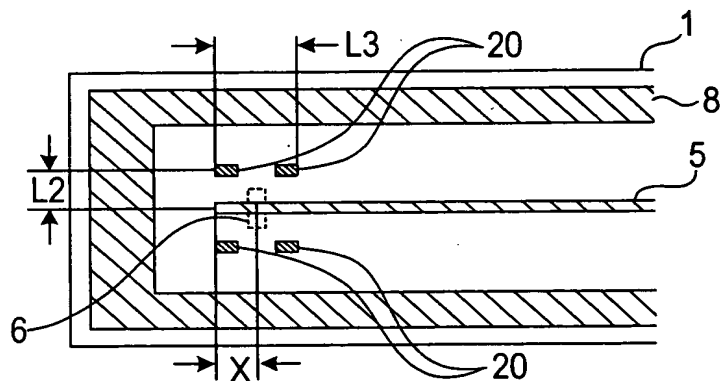


FIG. 4C

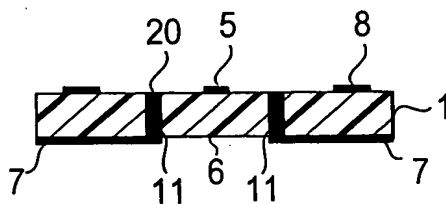


FIG. 4D

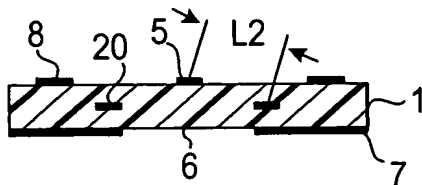
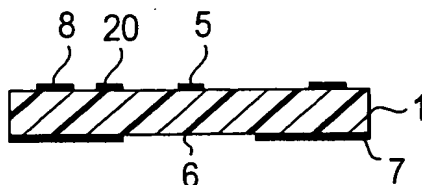


FIG. 4E



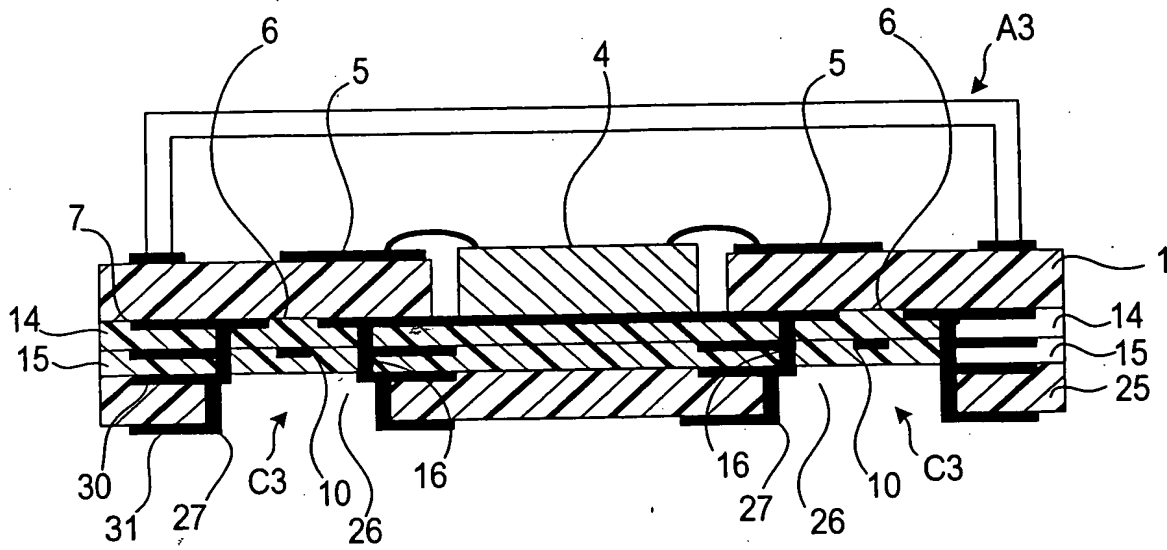
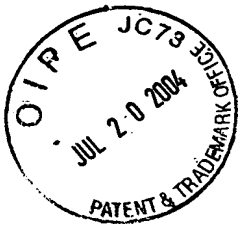


FIG. 5

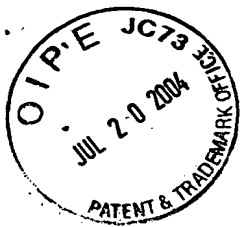


FIG. 6A

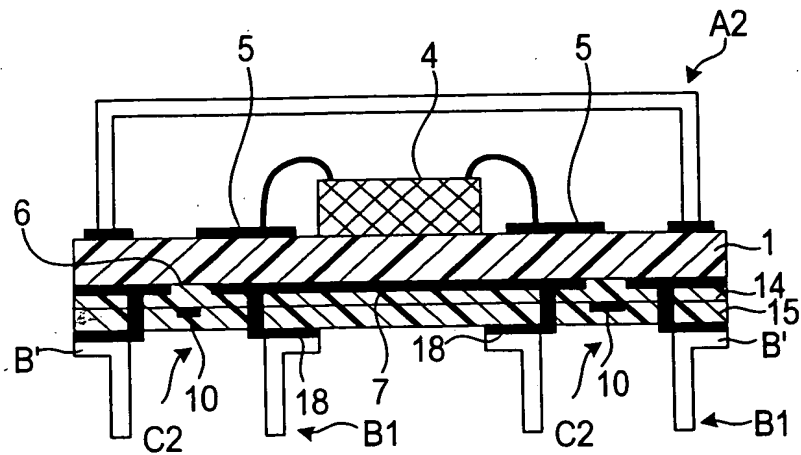


FIG. 6B

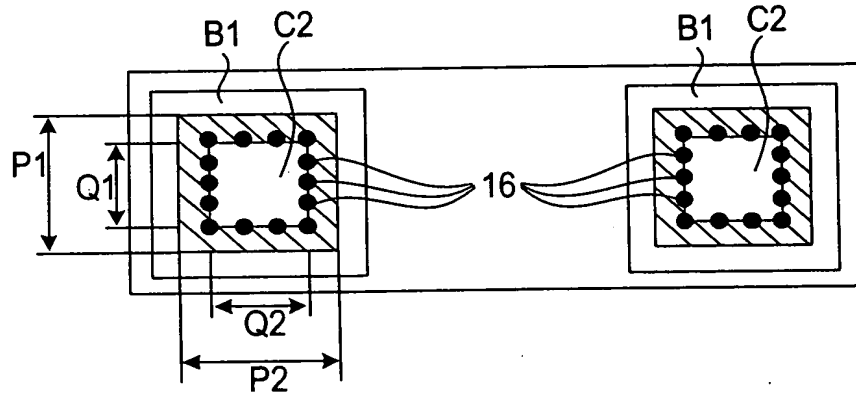


FIG. 6C

